

Tagore Technologies to Participate at IMS 2022

Chicago, IL, U.S. and Kolkata, India – June 14, 2022 – Delivering disruptive semiconductor solutions for over 10 years, Tagore Technology Inc. announces its participation at the International Microwave Symposium (IMS) 2022.

At the in-person event that takes place in Denver, Colorado, U.S., Tagore will showcase company's new Gallium Arsenide (GaAs) Low Noise Amplifiers (LNAs), Gallium Nitride (GaN) based Second Generation Radio Frequency (RF) switches as well as GaN power amplifier devices at **booth #10059**.

Leveraging wide bandgap capabilities, Tagore's proprietary technologies significantly reduce complexity, size and power consumption in a wide variety from 5G infrastructure to consumer, automotive and defense and public safety applications.

From June 19-24 June 2022, Tagore will also attend IMS2022 tradeshow. Further information can be found at [IMS 2022 | IMS Microwave Week | 19 - 24 June in Denver, Colorado \(ims-ieee.org\)](https://ims-ieee.org)

For more information on Tagore, visit www.tagoretech.com

About Tagore Technologies

Tagore Technology was founded in January 2011 to pioneer Gallium Nitride-on-Silicon (GaN-on-Si) semiconductor technology for Radio Frequency (RF) and power management applications. We are a fabless semiconductor company with design centers in Arlington Heights, Illinois, USA and Kolkata, India. Our R&D team is dedicated to developing disruptive solutions leveraging wide bandgap technologies that help address RF and power design challenges for our customers and accelerate time-to-market for a wide range of applications. For more information visit www.tagoretech.com